

# RJK0394DPA

# Silicon N Channel Power MOS FET Power Switching

REJ03G1785-0200 Rev.2.00 Apr 03, 2009

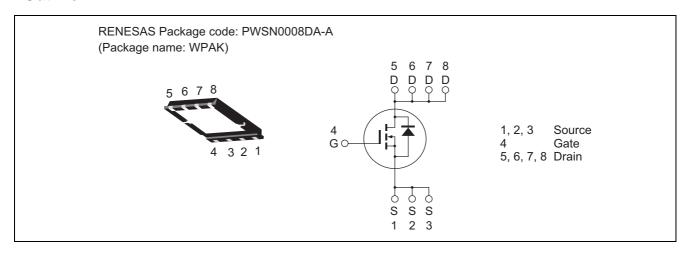
#### **Features**

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)}\!=4.1~\text{m}\Omega$  typ. (at  $V_{GS}\!=10~\text{V})$ 

- Pb-free
- Halogen-free

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	30	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	I <sub>D</sub>	35	A
Drain peak current	I <sub>D(pulse)</sub> Note1	140	A
Body-drain diode reverse drain current	I <sub>DR</sub>	35	A
Avalanche current	I <sub>AP</sub> Note 2	14	A
Avalanche energy	E <sub>AR</sub> Note 2	19.6	mJ
Channel dissipation	Pch Note3	35	W
Channel to case thermal impedance	θch-c Note3	3.57	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3.  $Tc = 25^{\circ}C$

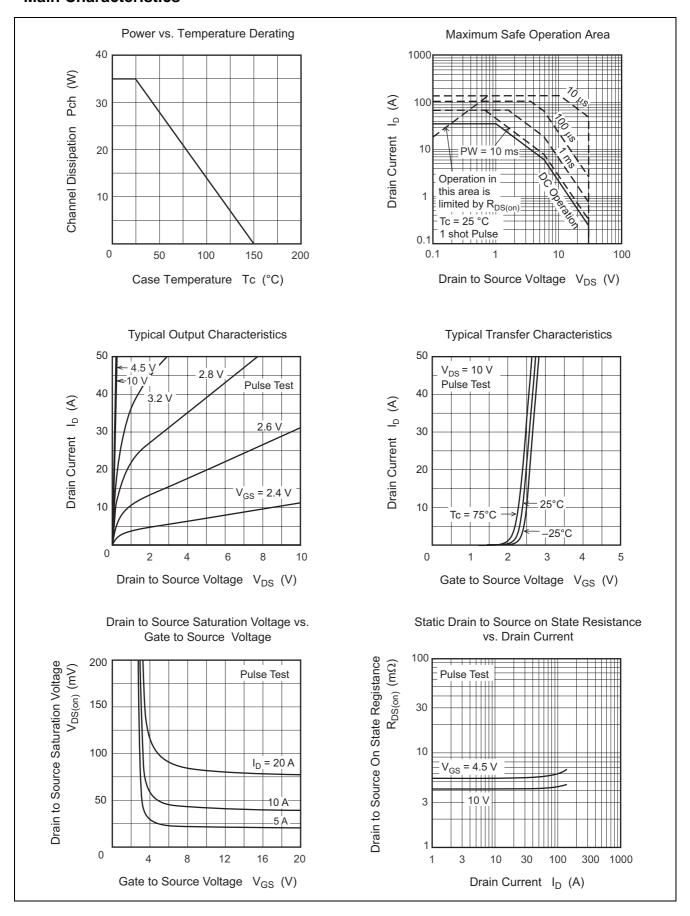
# **Electrical Characteristics**

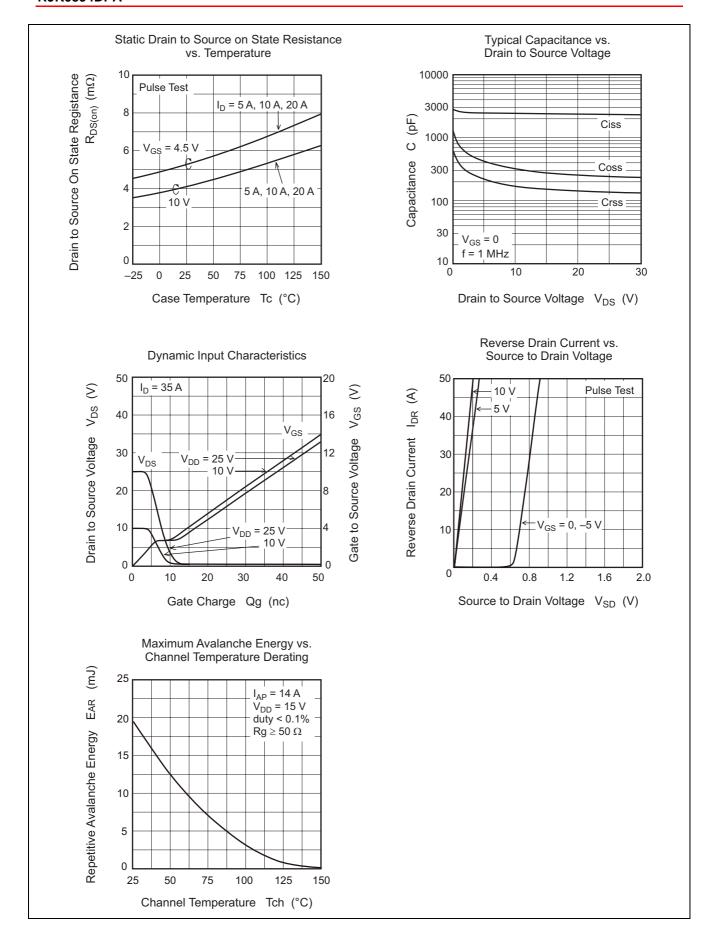
 $(Ta = 25^{\circ}C)$ 

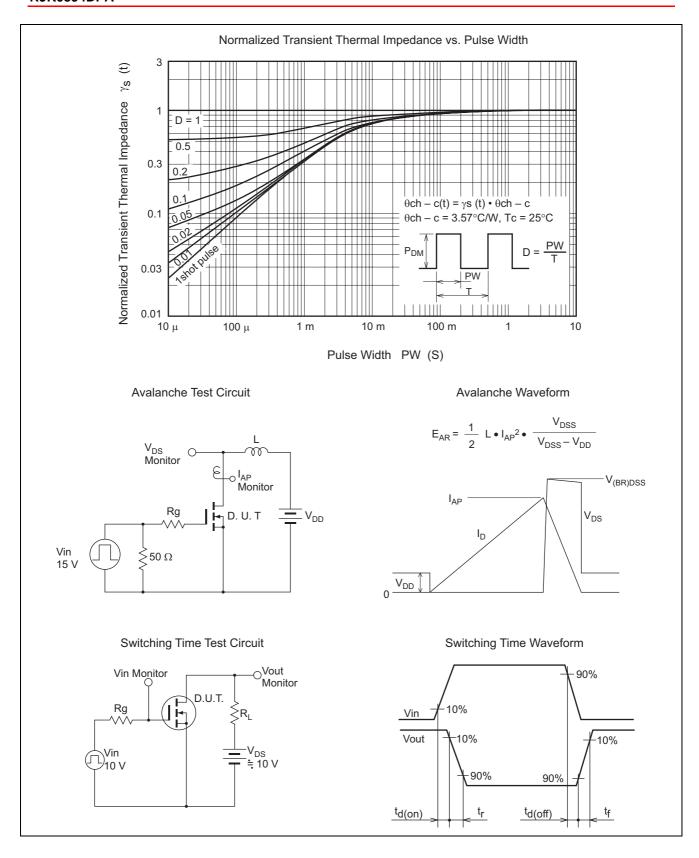
Symbol	Min	Тур	Max	Unit	Test Conditions
$V_{(BR)DSS}$	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
I <sub>GSS</sub>	_	_	± 0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
V <sub>GS(off)</sub>	1.2	_	2.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
R <sub>DS(on)</sub>	_	4.1	5.3	mΩ	$I_D = 17.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
R <sub>DS(on)</sub>	_	5.3	7.4	mΩ	$I_D = 17.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
y <sub>fs</sub>	_	95	_	S	$I_D = 35 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Ciss	_	2430	_	pF	V <sub>DS</sub> = 10 V
Coss	_	320	_	pF	$V_{GS} = 0$
Crss	_	170	_	pF	f = 1 MHz
Rg	_	1.4	_	Ω	
Qg	_	15.5	_	nC	V <sub>DD</sub> = 10 V
Qgs	_	7.1	_	nC	$V_{GS} = 4.5 \text{ V}$
Qgd	_	3.7	_	nC	$I_D = 35 \text{ A}$
t <sub>d(on)</sub>	_	13.0	_	ns	$V_{GS} = 10 \text{ V}, I_D = 17.5 \text{ A}$
t <sub>r</sub>	_	5.2	_	ns	V <sub>DD</sub> ≅ 10 V
t <sub>d(off)</sub>	_	45	_	ns	$R_L = 0.57 \Omega$
t <sub>f</sub>	_	6.2	_	ns	$Rg = 4.7 \Omega$
$V_{DF}$	_	0.83	1.08	V	$I_F = 35 \text{ A}, V_{GS} = 0^{\text{Note4}}$
t <sub>rr</sub>	_	22	_	ns	$I_F = 35 \text{ A}, V_{GS} = 0$ $di_F / dt = 100 \text{ A} / \mu \text{s}$
	V(BR)DSS IGSS IDSS VGS(off) RDS(on) RDS(on)  Yfs  Ciss Coss Crss Rg Qg Qgs Qgd td(on) tr td(off) tf VDF	V(BR)DSS         30           IGSS         —           VGS(off)         1.2           RDS(on)         —           RDS(on)         —           Iyfs          —           Ciss         —           Coss         —           Crss         —           Rg         —           Qg         —           Qgs         —           Qgd         —           td(on)         —           tf         —           VDF         —	V(BR)DSS         30         —           IGSS         —         —           IDSS         —         —           VGS(off)         1.2         —           RDS(on)         —         4.1           RDS(on)         —         5.3            yts          —         95           Ciss         —         2430           Coss         —         320           Crss         —         170           Rg         —         1.4           Qg         —         15.5           Qgs         —         7.1           Qgd         —         3.7           td(on)         —         13.0           tr         —         5.2           td(off)         —         45           tf         —         6.2           VDF         —         0.83	V(BR)DSS         30         —         —           IGSS         —         —         ± 0.1           IDSS         —         —         1           VGS(off)         1.2         —         2.5           RDS(on)         —         4.1         5.3           RDS(on)         —         5.3         7.4           Iyfs         —         95         —           Ciss         —         2430         —           Coss         —         320         —           Crss         —         170         —           Rg         —         1.4         —           Qg         —         15.5         —           Qgs         —         7.1         —           Qgd         —         3.7         —           td(on)         —         13.0         —           tr         —         5.2         —           tf         —         6.2         —           VDF         —         0.83         1.08	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

Notes: 4. Pulse test

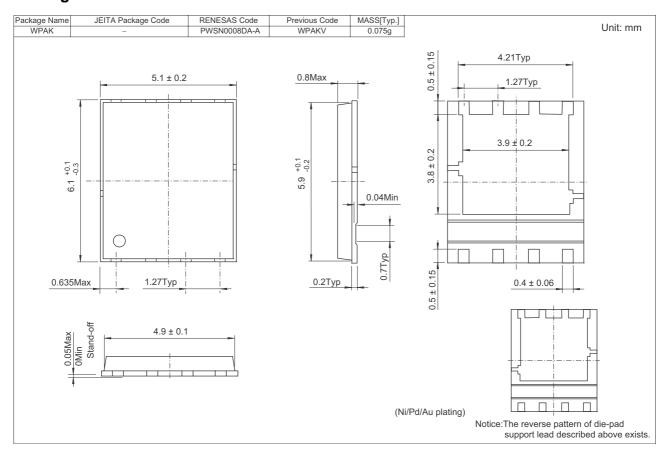
### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK0394DPA-00-J53	3000 pcs	Taping

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